## AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

- 1. (original) A complementary MISFET comprising:
- a first linear body including an N-type MISFET and a second linear body including a P-type MISFET; and
- a separation region arranged between said first linear body and said second linear body.
- 2. (original) The complementary MISFET of claim 1, wherein each cross section having a plurality of regions for forming said MISFET is continuously or intermittently formed in the longitudinal direction.
- 3.(currently amended) The complementary MISFET of claim 1
  [[or 2]], wherein said linear bodies and/or said separation
  region are formed of a material made of an organic
  semiconductor or electroconductive polymer.
- 4.(currently amended) An integrated circuit comprising the complementary MISFET of any one of claims 1 through 3 claim 1.
- 5.(currently amended) A production method of the complementary MISFET of any one of claims 1 through 3 claim 1, the method comprising the step of:

forming the separation region by coating or vapor depositing an insulating material between the plurality of linear bodies.

6. (currently amended) A production method of the complementary MISFET of any one of claims 1 through 3 claim 1, the method comprising the step of:

forming an insulating film on a surface of the linear body to thereby form the separation region.

- 7.(original) An integrated circuit comprising:
- a plurality of linear bodies, each having a cross section which has a plurality of regions for forming a circuit element formed in said linear body and which is continuously or intermittently formed in the longitudinal direction.
- 8.(original) The integrated circuit of claim 7, wherein said integrated circuit is a semiconductor memory, an image sensor, or a PLA.
- 9. (currently amended) The integrated circuit of claim 7 [[or 8]], wherein said linear bodies are formed of a material made of an organic semiconductor or electroconductive polymer.
- 10. (currently amended) The integrated circuit of any one of claims 4 and 7 through 9 claim 4, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.
- 11. (new) The complementary MISFET of claim 2, wherein said linear bodies and/or said separation region are formed of a material made of an organic semiconductor or electroconductive polymer.
- 12. (new) An integrated circuit comprising the complementary MISFET of claim 2.

- 13. (new) An integrated circuit comprising the complementary MISFET of claim 3.
- 14. (new) A production method of the complementary MISFET of claim 2, the method comprising the step of:

forming the separation region by coating or vapor depositing an insulating material between the plurality of linear bodies.

15. (new) A production method of the complementary MISFET of claim 3, the method comprising the step of:

forming the separation region by coating or vapor depositing an insulating material between the plurality of linear bodies.

16. (new) A production method of the complementary MISFET of claim 2, the method comprising the step of:

forming an insulating film on a surface of the linear body to thereby form the separation region.

17. (new) A production method of the complementary MISFET of claim 3, the method comprising the step of:

forming an insulating film on a surface of the linear body to thereby form the separation region.

18. (new) The integrated circuit of claim 8, wherein said linear bodies are formed of a material made of an organic semiconductor or electroconductive polymer.

- 19. (new) The integrated circuit of claim 7, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.
- 20. (new) The integrated circuit of claim 8, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.